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In this contribution, the test beam measurements of novel passive CMOS silicon strip sensors performed at the DESY-II test beam facility are presented. The sensor is processed by a European foundry, in a 150 nm CMOS technology and has three different strips design to study. The sensors have two different strip lengths and are formed by stitching of individual reticles. The main focus of this test beam measurement on the passive CMOS sensors is to study the charge collection, to determine the hit detection efficiency and to examine the performance of the stitching.

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